

Supplementary Information: Aqueous-based synthesis of gallium tungsten oxide thin film dielectrics

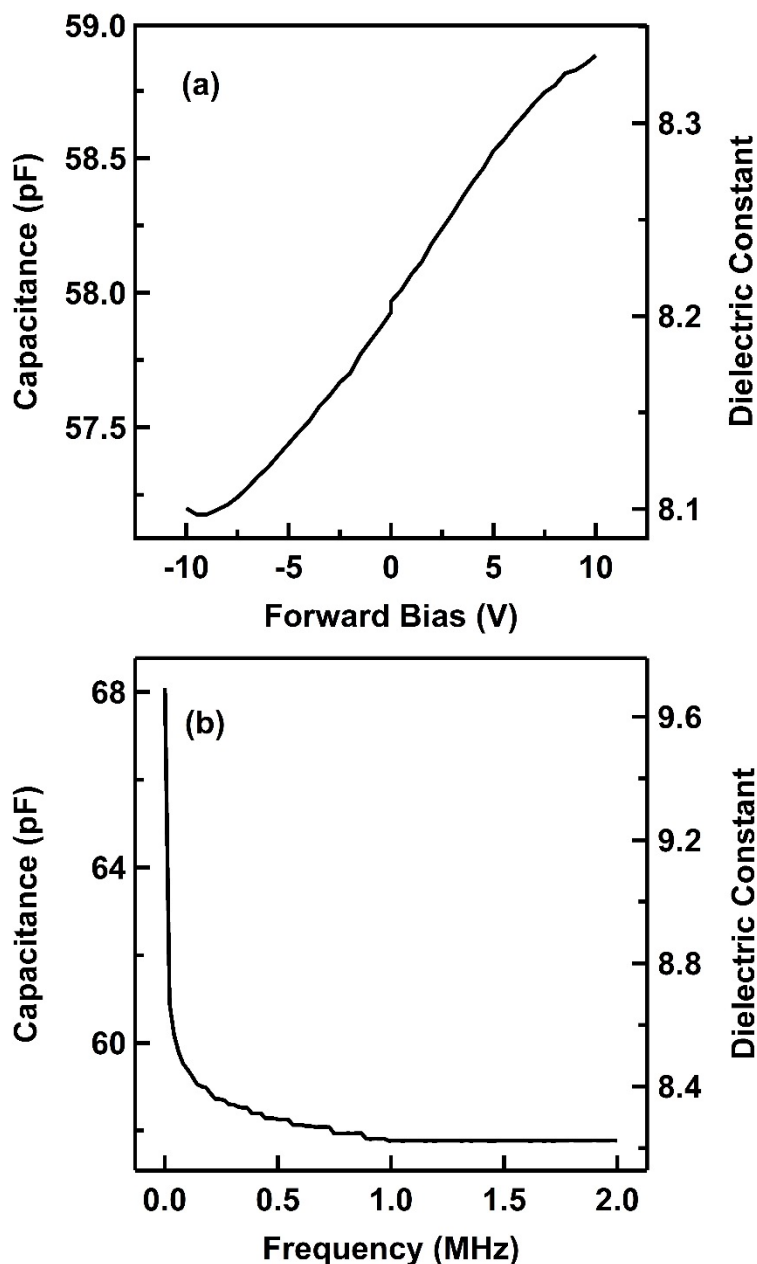


Figure S1: Capacitance-voltage measurement at frequency 1 MHz (a) and capacitance-frequency measurement at no applied bias (b) for a representative $\text{Ga}_{2-x}\text{W}_{x/2}\text{O}_{3-\delta}$ thin film (17.1 at% W, 600 °C anneal). The corresponding dielectric constant was estimated assuming a parallel plate capacitor.